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IN THE ABSTRACT:

Please amend the Abstract as follows:

ABSTRACT OF THE DISCLOSURE

A method for fabricating a semiconductor device has the steps of forming a conductive film on a substrate, forming an insulating film such that the conductive film is covered with the insulating film, forming, in the insulating film, a hole having a bottom portion not reaching the conductive film by using a mask layer having a first opening pattern, and forming, in the insulating film, an opening for exposing the conductive film by using a mask layer having a second opening pattern having an opening diameter larger than an opening diameter of the first opening pattern. An obtuse angle is formed between a wall surface of the opening and a bottom surface of the opening.